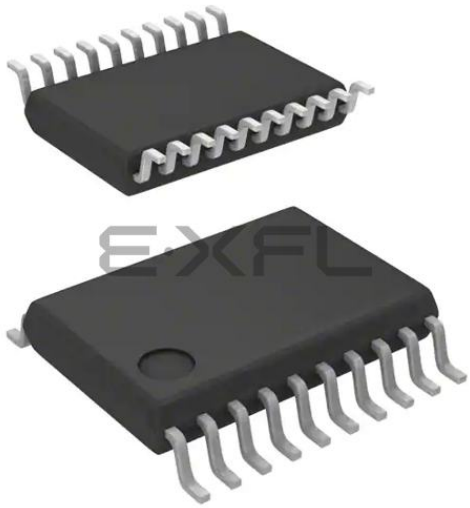
Renesas Electronics America Inc - R5F21191DSP#U0 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	384 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21191dsp-u0

1. Overview

These MCUs are fabricated using a high-performance silicon gate CMOS process, embedding the R8C/Tiny Series CPU core, and is packaged in a 20-pin molded-plastic LSSOP, SDIP or a 28-pin plastic molded-HWQFN. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/19 Group has on-chip data flash ROM (1 KB × 2 blocks).
The difference between the R8C/18 Group and R8C/19 Group is only the presence or absence of data flash ROM. Their peripheral functions are the same.

1.1 Applications

Electric household appliances, office equipment, housing equipment (sensors, security systems), general industrial equipment, audio equipment, etc.

1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/18 Group and Table 1.2 outlines the Functions and Specifications for R8C/19 Group.

Table 1.1 Functions and Specifications for R8C/18 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operation mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.3 Product Information for R8C/18 Group**
Peripheral Functions	Ports	I/O ports: 13 pins (including LED drive port) Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Input capture and output compare circuits)
	Serial interfaces	1 channel Clock synchronous serial I/O, UART 1 channel UART
	Comparator	1-bit comparator: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable, count source protection mode
	Interrupts	Internal: 10 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	2 circuits • Main clock oscillation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function
	Oscillation stop detection function	Main clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, comparator stopped) Typ. 5 mA (VCC = 3.0V, f(XIN) = 10 MHz, comparator stopped) Typ. 35 μA (VCC = 3.0 V, wait mode, peripheral clock off) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D version)
Package		20-pin molded-plastic LSSOP
		20-pin molded-plastic SDIP
		28-pin molded-plastic HWQFN

Table 1.2 Functions and Specifications for R8C/19 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operation mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.4 Product Information for R8C/19 Group**
Peripheral Functions	Ports	I/O ports: 13 pins (including LED drive port) Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Input capture and output compare circuits)
	Serial interfaces	1 channel Clock synchronous serial I/O, UART 1 channel UART
	Comparator	1-bit comparator: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable, count source protection mode
	Interrupts	Internal: 10 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	2 circuits • Main clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function
	Oscillation stop detection function	Main clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, comparator stopped) Typ. 5 mA (VCC = 3.0 V, f(XIN) = 10MHz, comparator stopped) Typ. 35 μA (VCC = 3.0 V, wait mode, peripheral clock off) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash) 1,000 times (program ROM)
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D version)
Package		20-pin molded-plastic LSSOP
		20-pin molded-plastic SDIP
		28-pin molded-plastic HWQFN

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.

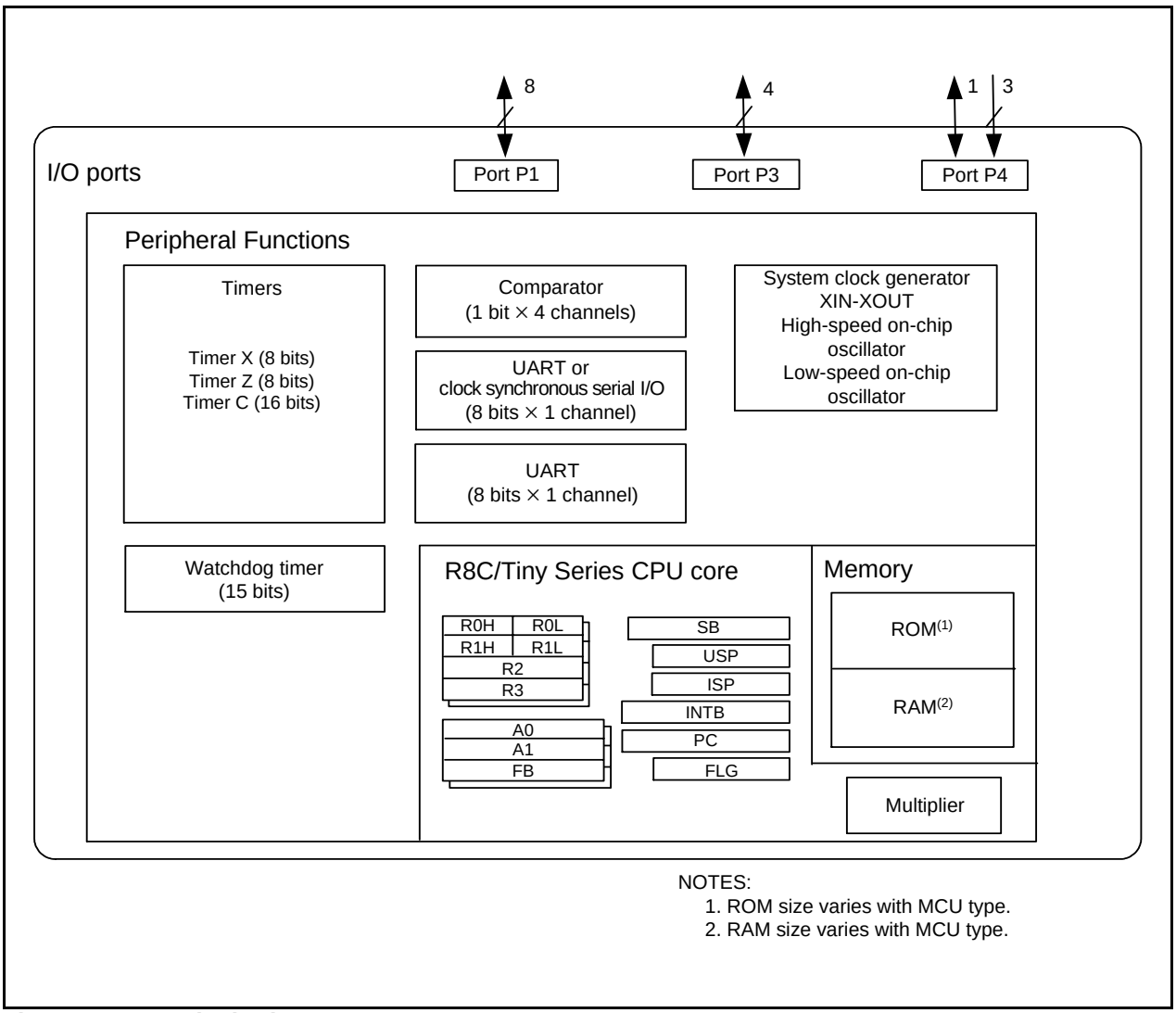


Figure 1.1 Block Diagram

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments for PLSP0020JB-A Package (Top View), Figure 1.5 shows Pin Assignments for PRDP0020BA-A Package (Top View) and Figure 1.6 shows Pin Assignments for PWQN0028KA-B Package (Top View).

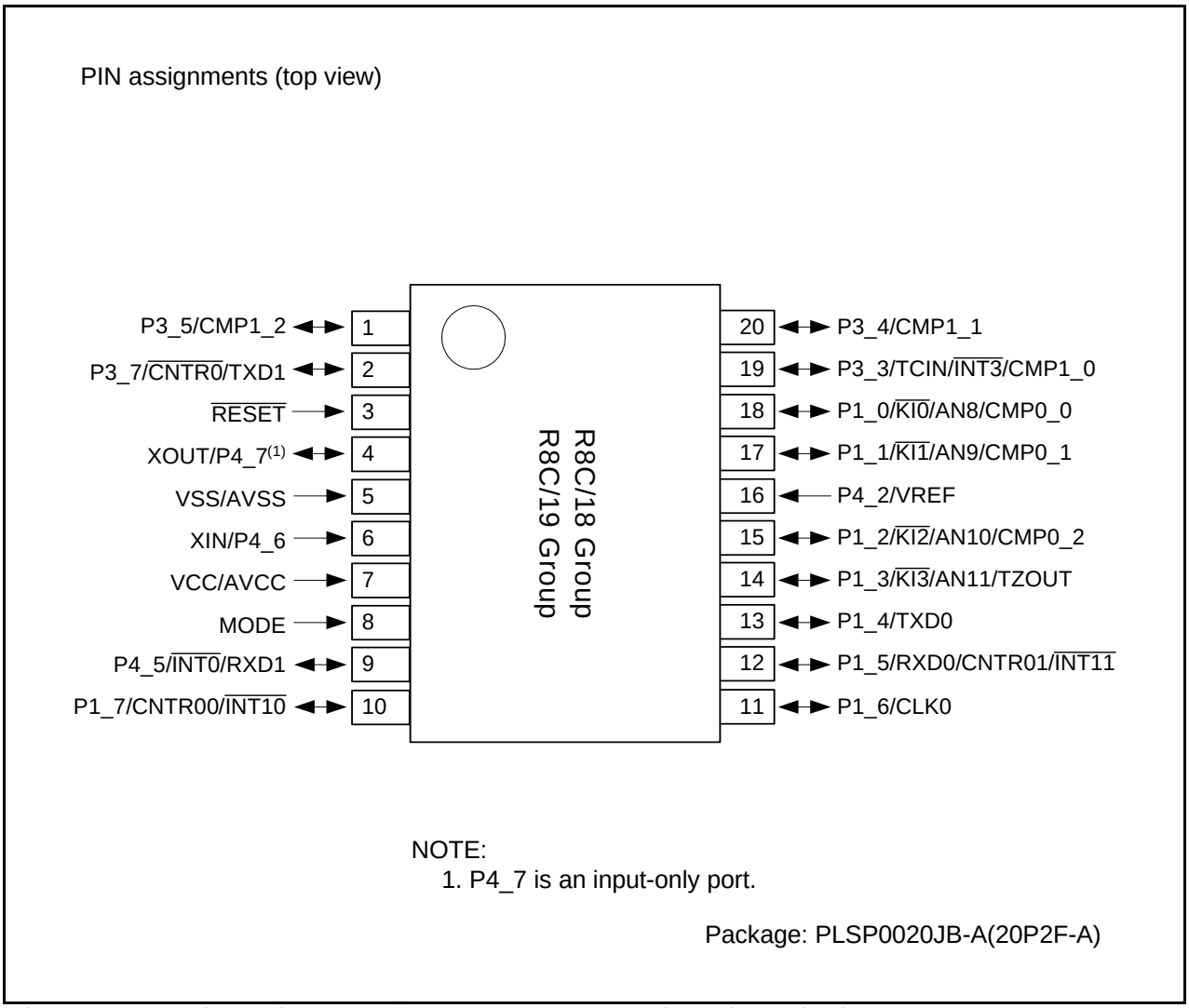


Figure 1.4 Pin Assignments for PLSP0020JB-A Package (Top View)

1.6 Pin Functions

Table 1.5 lists Pin Functions, Table 1.6 lists Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A packages, and Table 1.7 lists Pin Name Information by Pin Number of PWQN0028KA-B package.

Table 1.5 Pin Functions

Type	Symbol	I/O Type	Description
Power supply input	VCC VSS	I	Apply 2.7 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the comparator Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
Main clock input	XIN	I	These pins are provided for main clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
Main clock output	XOUT	O	
$\overline{\text{INT}}$ interrupt	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer X	CNTR0	I/O	Timer X I/O pin
	$\overline{\text{CNTR0}}$	O	Timer X output pin
Timer Z	TZOUT	O	Timer Z output pin
Timer C	TCIN	I	Timer C input pin
	CMP0_0 to CMP0_2, CMP1_0 to CMP1_2	O	Timer C output pins
Serial interface	CLK0	I/O	Transfer clock I/O pin
	RXD0, RXD1	I	Serial data input pins
	TXD0, TXD1	O	Serial data output pins
Reference voltage input	VREF	I	Reference voltage input pin to comparator
Comparator	AN8 to AN11	I	Analog input pins to comparator
I/O port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_3 also function as LED drive ports.
Input port	P4_2, P4_6, P4_7	I	Input-only ports

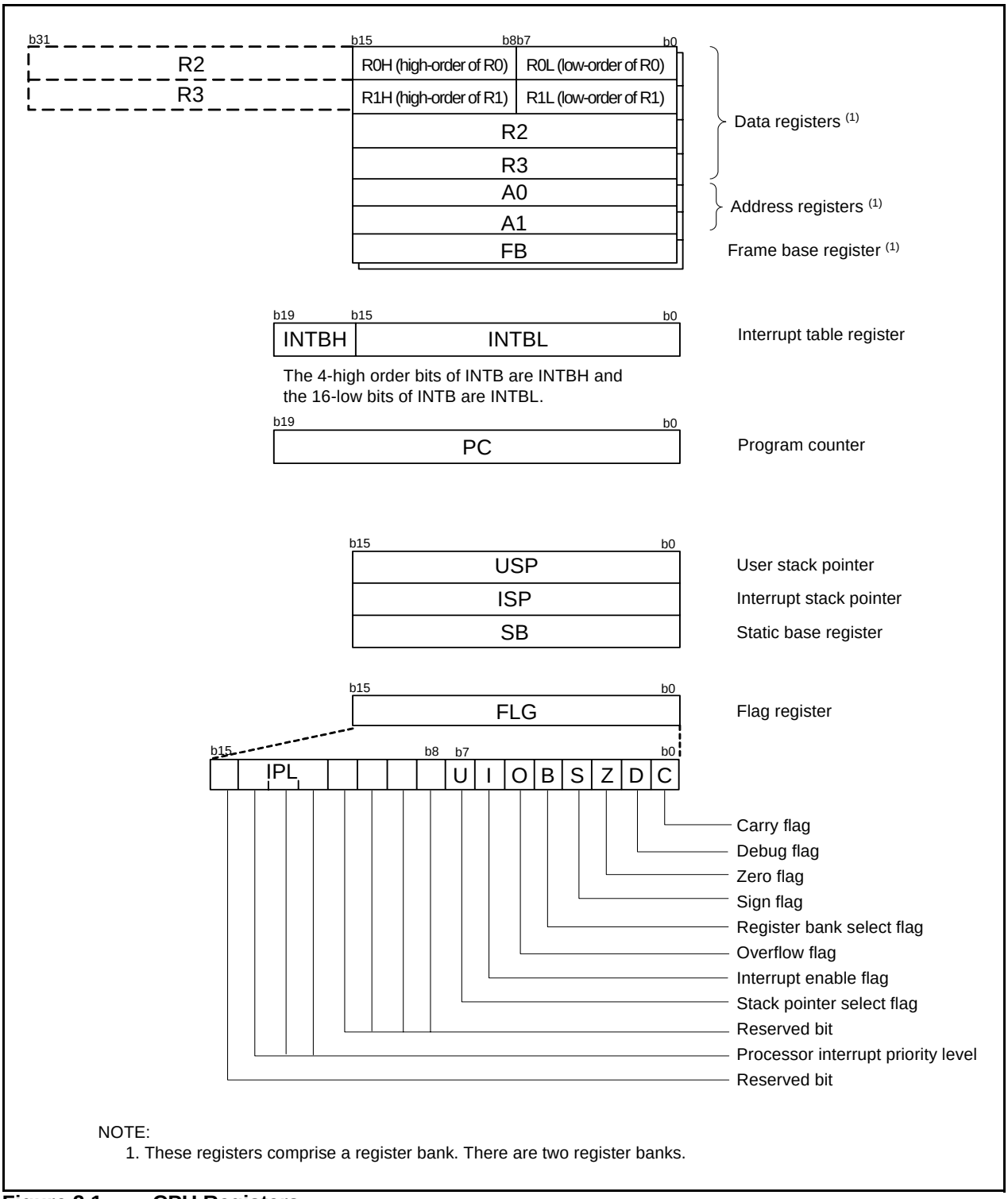
I: Input O: Output I/O: Input and output

Table 1.6 Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A packages

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules			
			Interrupt	Timer	Serial Interface	Comparator
1		P3_5		CMP1_2		
2		P3_7		$\overline{\text{CNTR0}}$	TXD1	
3	$\overline{\text{RESET}}$					
4	XOUT	P4_7				
5	VSS/AVSS					
6	XIN	P4_6				
7	VCC/AVCC					
8	MODE					
9		P4_5	$\overline{\text{INT0}}$		RXD1	
10		P1_7	$\overline{\text{INT10}}$	CNTR00		
11		P1_6			CLK0	
12		P1_5	$\overline{\text{INT11}}$	CNTR01	RXD0	
13		P1_4			TXD0	
14		P1_3	$\overline{\text{KI3}}$	TZOUT		AN11
15		P1_2	$\overline{\text{KI2}}$	CMP0_2		AN10
16	VREF	P4_2				
17		P1_1	$\overline{\text{KI1}}$	CMP0_1		AN9
18		P1_0	$\overline{\text{KI0}}$	CMP0_0		AN8
19		P3_3	$\overline{\text{INT3}}$	TCIN/CMP1_0		
20		P3_4		CMP1_1		

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



NOTE:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic and logic operations. A1 is analogous to A0. A1 can be combined with A0 and used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide, indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointer (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains a carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when the operation results in an overflow; otherwise to 0.

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

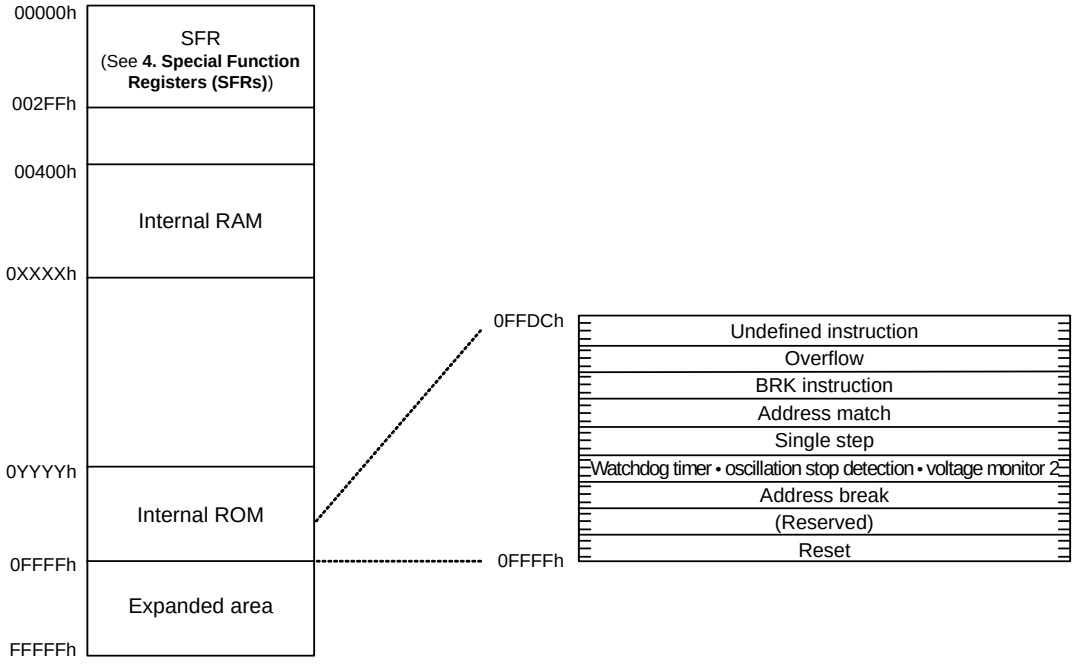
2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/18 Group

Figure 3.1 is a Memory Map of R8C/18 Group. The R8C/18 Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM area is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



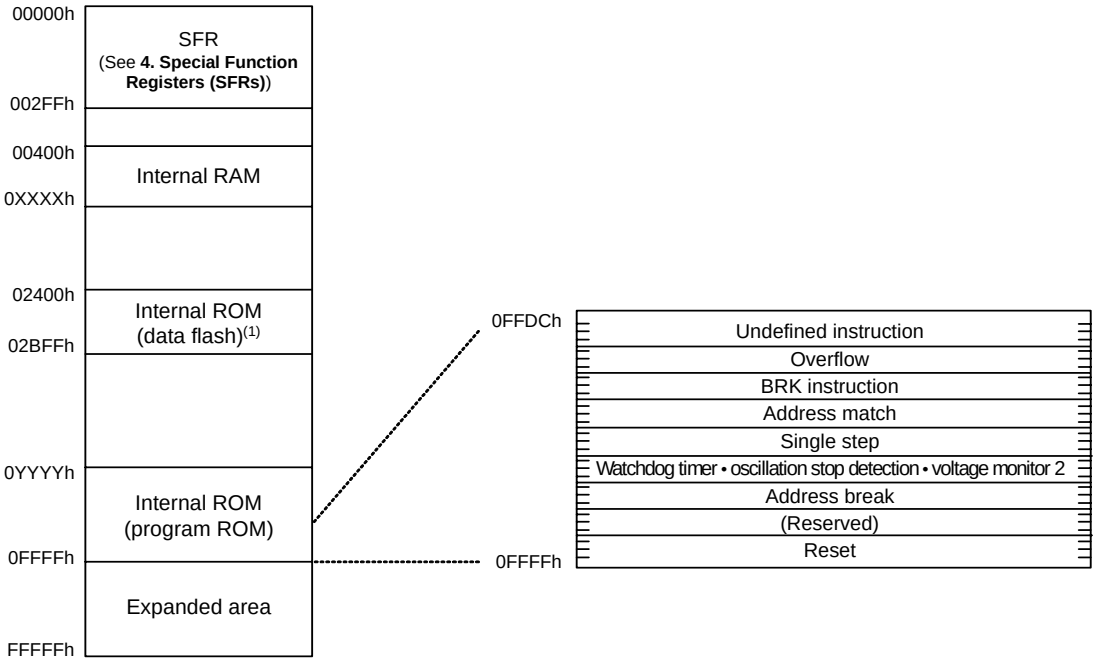
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21184SP, R5F21184DSP, R5F21184DD, R5F21184NP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21183SP, R5F21183DSP, R5F21183DD, R5F21183NP	12 Kbytes	0D000h	768 bytes	006FFh
R5F21182SP, R5F21182DSP, R5F21182DD, R5F21182NP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21181SP, R5F21181DSP, R5F21181DD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.1 Memory Map of R8C/18 Group

3.2 R8C/19 Group

Figure 3.2 is a Memory Map of R8C/19 Group. The R8C/19 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21194SP, R5F21194DSP, R5F21194DD, R5F21194NP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21193SP, R5F21193DSP, R5F21193DD, R5F21193NP	12 Kbytes	0D000h	768 bytes	006FFh
R5F21192SP, R5F21192DSP, R5F21192DD, R5F21192NP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21191SP, R5F21191DSP, R5F21191DD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.2 Memory Map of R8C/19 Group

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}	Supply voltage	V_{CC} = AV_{CC}	-0.3 to 6.5	V
AV_{CC}	Analog supply voltage	V_{CC} = AV_{CC}	-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC}+0.3	V
V_O	Output voltage		-0.3 to V_{CC}+0.3	V
P_d	Power dissipation	T_{opr} = 25°C	300	mW
T_{opr}	Operating ambient temperature		-20 to 85 / -40 to 85 (D version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}	Supply voltage			2.7	–	5.5	V
AV_{CC}	Analog supply voltage			–	V_{CC}	–	V
V_{SS}	Supply voltage			–	0	–	V
AV_{SS}	Analog supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH\ (peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak output “H” current			–	–	-10	mA
$I_{OH(avg)}$	Average output “H” current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL\ (peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_3		–	–	10	mA
		P1_0 to P1_3	Drive capacity HIGH	–	–	30	mA
			Drive capacity LOW	–	–	10	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_3		–	–	5	mA
		P1_0 to P1_3	Drive capacity HIGH	–	–	15	mA
			Drive capacity LOW	–	–	5	mA
$f_{(XIN)}$	Main clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Typical values when average output current is 100 ms.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/18 Group	100(3)	–	–	times
		R8C/19 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(8)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to Suspend can be applied to the request.However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. -40 °C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

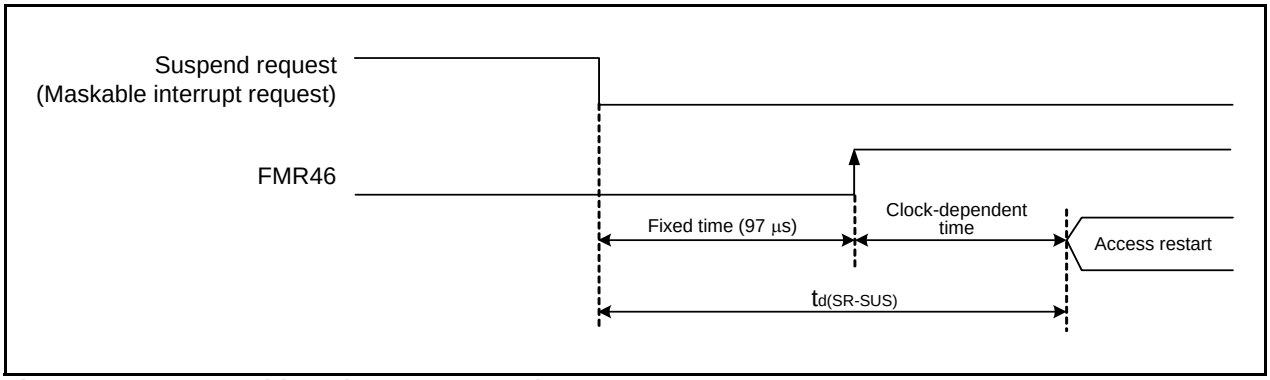


Figure 5.2 Transition Time to Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3)		2.70	2.85	3.00	V
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.7	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Ensure that $V_{det2} > V_{det1}$.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.00	3.30	3.60	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Ensure that $V_{det2} > V_{det1}$.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

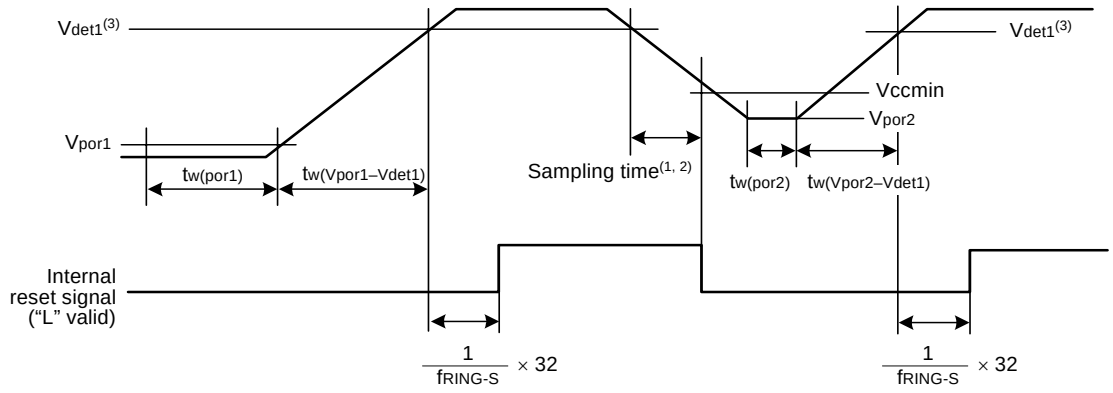
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por2}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	V_{det1}	V
$t_{w(Vpor2-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted(1)	-20°C ≤ Topr ≤ 85°C, $t_{w(por2)}$ ≥ 0s(3)	–	–	100	ms

NOTES:
1. This condition is not applicable when using with Vcc ≥ 1.0 V.
2. When turning power on after the time to hold the external power below effective voltage (V_{por1}) exceeds10 s, refer to **Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)**.
3. $t_{w(por2)}$ is the time to hold the external power below effective voltage (V_{por2}).

Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	0.1	V
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 30 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	1	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 1 s(2)	–	–	0.5	ms

NOTES:
1. When not using voltage monitor 1, use with Vcc ≥ 2.7 V.
2. $t_{w(por1)}$ is the time to hold the external power below effective voltage (V_{por1}).



NOTES:
1. Hold the voltage inside the MCU operation voltage range (Vccmin or above) within the sampling time.
2. The sampling clock can be selected. Refer to **7. Voltage Detection Circuit** for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **7. Voltage Detection Circuit** for details.

Figure 5.3 Reset Circuit Electrical Characteristics

Table 5.12 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
VOH	Output “H” voltage	Except XOUT	IOH = -5 mA		Vcc – 2.0	–	Vcc	V
			IOH = -200 µA		Vcc – 0.3	–	Vcc	V
		XOUT	Drive capacity HIGH	IOH = -1 mA	Vcc – 2.0	–	Vcc	V
			Drive capacity LOW	IOH = -500 µA	Vcc – 2.0	–	Vcc	V
VOL	Output “L” voltage	Except P1_0 to P1_3, XOUT	IOL = 5 mA		–	–	2.0	V
			IOL = 200 µA		–	–	0.45	V
		P1_0 to P1_3	Drive capacity HIGH	IOL = 15 mA	–	–	2.0	V
			Drive capacity LOW	IOL = 5 mA	–	–	2.0	V
			Drive capacity LOW	IOL = 200 µA	–	–	0.45	V
		XOUT	Drive capacity HIGH	IOL = 1 mA	–	–	2.0	V
			Drive capacity LOW	IOL = 500 µA	–	–	2.0	V
VT+-VT-	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	1.0	V
		$\overline{RESET}$			0.2	–	2.2	V
IIH	Input “H” current		VI = 5 V		–	–	5.0	µA
IIL	Input “L” current		VI = 0 V		–	–	-5.0	µA
RPULLUP	Pull-up resistance		VI = 0 V		30	50	167	kΩ
RfXIN	Feedback resistance	XIN			–	1.0	–	MΩ
fRING-S	Low-speed on-chip oscillator frequency				40	125	250	kHz
VRAM	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. Vcc = 4.2 to 5.5 V at Topr = -20 to 85 °C / -40 to 85 °C, f(XIN) = 20 MHz, unless otherwise specified.

Timing Requirements
(Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Ta = 25 °C) [Vcc = 5 V]

Table 5.14 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

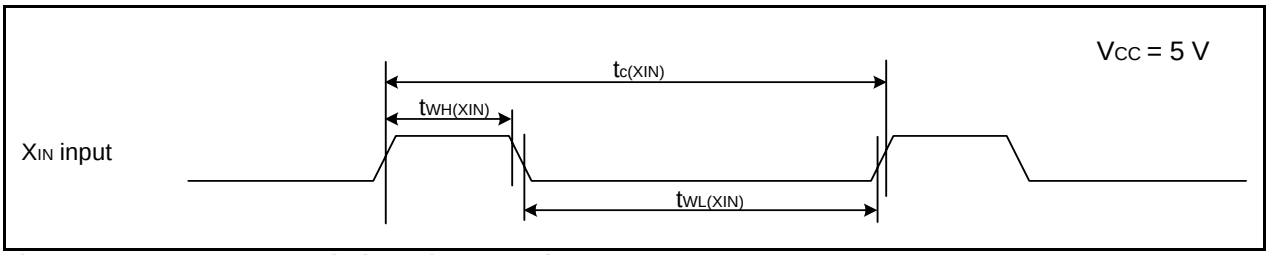


Figure 5.4 XIN Input Timing Diagram when Vcc = 5 V

Table 5.15 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CNTR0)}$	CNTR0 input cycle time	100	–	ns
$t_{WH(CNTR0)}$	CNTR0 input “H” width	40	–	ns
$t_{WL(CNTR0)}$	CNTR0 input “L” width	40	–	ns

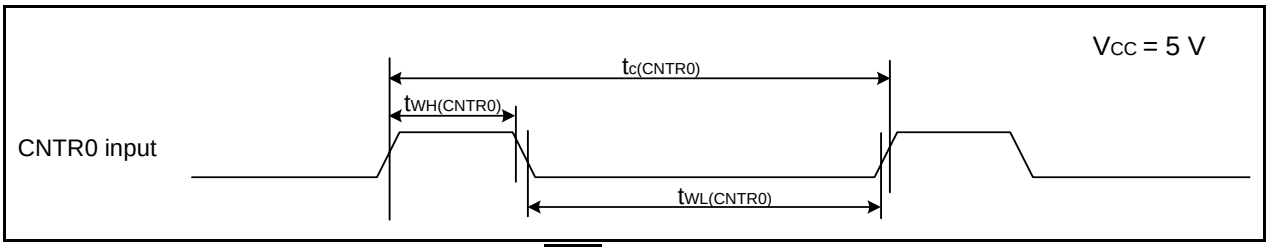


Figure 5.5 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input Timing Diagram when Vcc = 5 V

Table 5.16 TCIN Input, $\overline{\text{INT3}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TCIN)}$	TCIN input cycle time	400(1)	–	ns
$t_{WH(TCIN)}$	TCIN input “H” width	200(2)	–	ns
$t_{WL(TCIN)}$	TCIN input “L” width	200(2)	–	ns

NOTES:
1. When using timer C input capture mode, adjust the cycle time to (1/timer C count source frequency x 3) or above.
2. When using timer C input capture mode, adjust the pulse width to (1/timer C count source frequency x 1.5) or above.

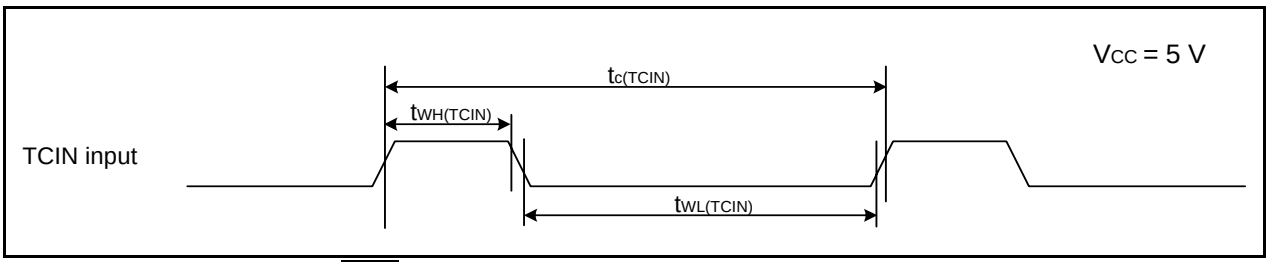


Figure 5.6 TCIN Input, $\overline{\text{INT3}}$ Input Timing Diagram when Vcc = 5 V

Table 5.20 Electrical Characteristics (4) [Vcc = 3V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are Vss, comparator is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	13	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	7	12	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.6	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	7.5	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	100	280	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	37	74	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	35	70	µA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.7	3.0	µA